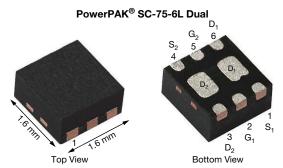


Dual N-Channel 20 V MOSFET



Marking code: CA

PRODUCT SUMMARY										
V _{DS} (V)	20									
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.216									
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 2.5 \text{ V}$	0.268									
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 1.8 \text{ V}$	0.375									
Q _g typ. (nC)	1.2									
I _D (A) a, g	1.5									
Configuration	Dual									

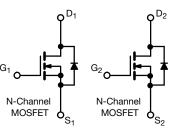
FEATURES

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK® SC-75 package
 - Small footprint area
 - Low on-resistance
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT HALOGEN FREE

APPLICATIONS

- · Load switch, PA switch, and battery switch for portable devices
- DC/DC converter



ORDERING INFORMATION						
Package	PowerPAK SC-75					
Lead (Pb)-free and halogen-free	SiB912DK-T1-GE3					

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)								
PARAMETER		SYMBOL	LIMIT	UNIT				
Drain-source voltage		V_{DS}	20	V				
Gate-source voltage		V_{GS}	±8	v				
	T _C = 25 °C		1.5 ^a					
Continuous drain current (T = 150 °C)	T _C = 70 °C		1.5 ^a					
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	- I _D	1.5 ^{a, b, c}	7				
	T _A = 70 °C		1.4 ^{b, c}	A				
Pulsed drain current		I _{DM}	5	7				
Continuous source-drain diode current	T _C = 25 °C		1.5 ^a					
Continuous source-drain diode current	T _A = 25 °C	l _S	0.9 ^{b, c}					
	T _C = 25 °C		3.1					
Maximum navvar dissination	T _C = 70 °C		2	w				
Maximum power dissipation	T _A = 25 °C	P _D	1.1 ^{b, c}	∀ • • • • • • • • • • • • • • • • • • •				
	T _A = 70 °C		0.7 b, c	7				
Operating junction and storage temperature range	ge	T _J , T _{stg}	-55 to +150	°C				
Soldering recommendations (peak temperature)	d, e		260	7				

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	90	115	°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	32	40	C/VV				

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- 6. See solder profile (<u>www.vishav.com/doc?73257</u>). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components Maximum under steady state conditions is 125 °C/W
- g. Based on $T_C = 25\ ^{\circ}C$



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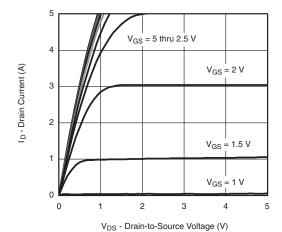
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	<u>.</u>			•		ı
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	L 050 A	-	22	-	mV/°C
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-2	-	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.4	-	1	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	-	-	±100	nA
Zana mata walta na alusin awamat	,	V _{DS} = 20 V, V _{GS} = 0 V	-	-	1	μΑ
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10	
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	5	-	-	Α
	, ,	V _{GS} = 4.5 V, I _D = 1.8 A	-	0.180	0.216	Ω
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 1.6 \text{ A}$	-	0.223	0.268	
		$V_{GS} = 1.8 \text{ V}, I_D = 0.3 \text{ A}$	-	0.300	0.375	
Forward transconductance a	9 _{fs}	V _{DS} = 10 V, I _D = 1.8 A	-	3	-	S
Dynamic ^b						
Input capacitance	itance C _{iss}					
Output capacitance	Coss	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	24	-	pF
Reverse transfer capacitance	C _{rss}		-	11	-	
-		$V_{DS} = 10 \text{ V}, V_{GS} = 8 \text{ V}, I_{D} = 1.8 \text{ A}$	-	2	3	nC
Total gate charge	Qg		-	1.2	1.8	
Gate-source charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 1.8 \text{ A}$	-	0.3	-	
Gate-drain charge	Q _{qd}		-	0.15	-	
Gate resistance	R_g	f = 1 MHz	0.5	2.5	5	Ω
Turn-on delay time	t _{d(on)}		-	5	10	
Rise time	t _r	$V_{DD} = 10 \text{ V}, R_L = 7.1 \Omega,$	-	10	20	
Turn-off delay time	t _{d(off)}	$I_D \cong 1.4 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	24	36	
Fall time	t _f			8	16	1
Turn-on delay time	t _{d(on)}		-	2	4	ns
Rise time	t _r	$V_{DD} = 10 \text{ V}, R_L = 7.1 \Omega,$	-	9	18	
Turn-off delay time	t _{d(off)}	$I_D \cong 1.4 \text{ A}, V_{GEN} = 8 \text{ V}, R_g = 1 \Omega$	-	8	16	
Fall time	t _f		-	7	14	
Drain-Source Body Diode Characterist	ics					
Continuous source-drain diode current c	I _S	T _C = 25 °C	-	-	1.5	
Pulse diode forward current	I _{SM}		-	-	5	Α
Body diode voltage	V _{SD}	I _S = 1.4 A, V _{GS} = 0 V	-	0.7	1.2	٧
Body diode reverse recovery time	t _{rr}	- 40	-	9	18	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = 1.4 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	3	6	nC
Reverse recovery fall time	t _a	$T_{J} = 25 ^{\circ}\text{C}$	-	6	-	ns
Reverse recovery rise time	t _b	-	_	3		

Notes

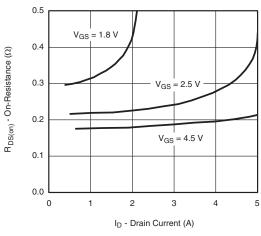
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Package limited

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

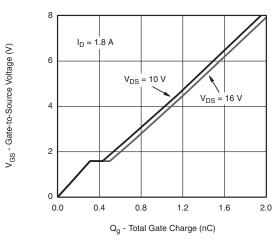




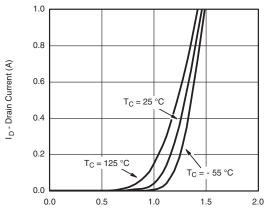
Output Characteristics



On-Resistance vs. Drain Current and Gate Voltage

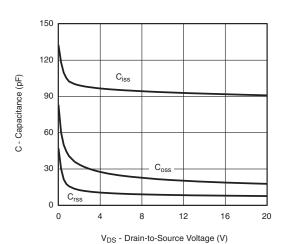


Gate Charge

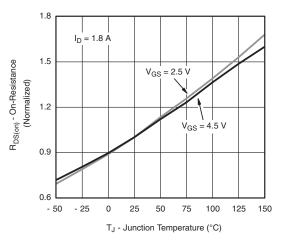


V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics

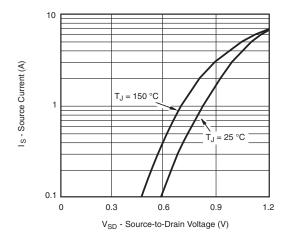


Capacitance

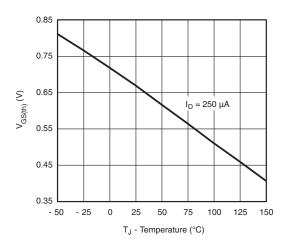


On-Resistance vs. Junction Temperature

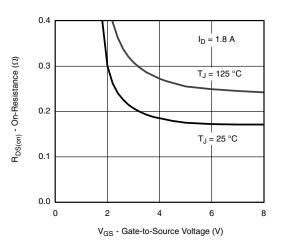




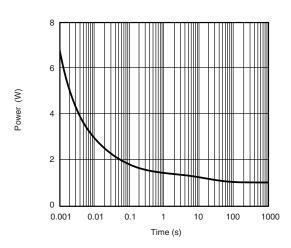
Source-Drain Diode Forward Voltage



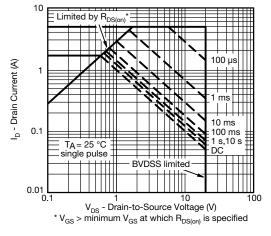
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

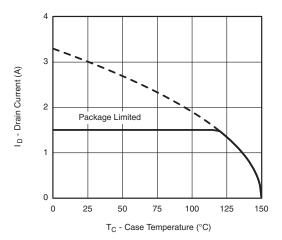


Single Pulse Power, Junction-to-Ambient

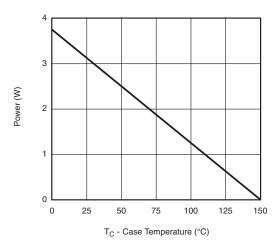


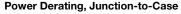
Safe Operating Area, Junction-to-Case

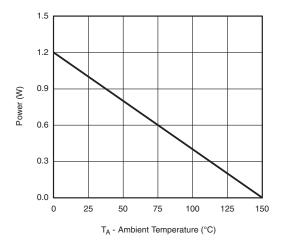




Current Derating a





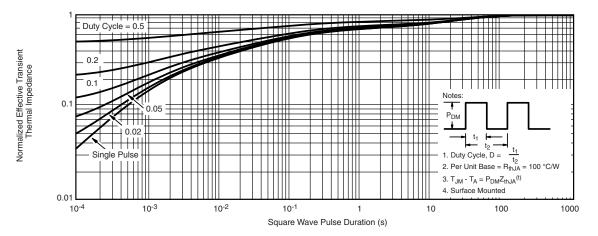


Power Derating, Junction-to-Ambient

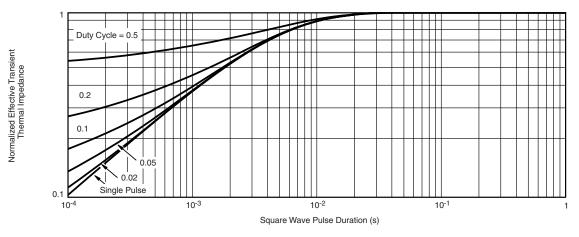
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



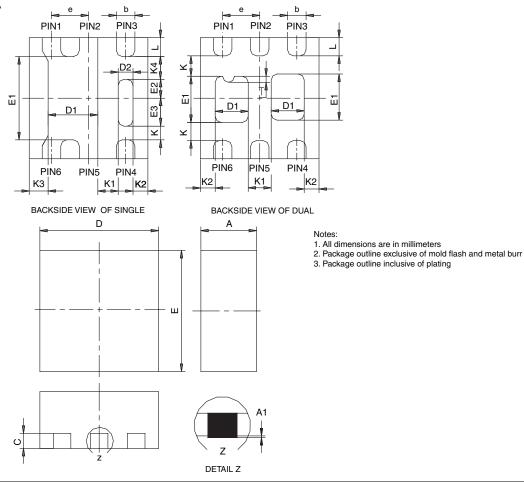
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68883.





PowerPAK® SC75-6L



	SINGLE PAD						DUAL PAD						
DIM	M	ILLIMETER	RS		INCHES		M	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021	
D2	0.10	0.20	0.30	0.004	0.008	0.012						1	
E	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028	
E2	0.20	0.25	0.30	0.008	0.010	0.012						1	
E3	0.32	0.37	0.42	0.013	0.015	0.017						1	
е		0.50 BSC			0.020 BSC			0.50 BSC			0.020 BSC		
K		0.180 TYP			0.007 TYP)	0.245 TYP			0.010 TYP			
K 1	0.275 TYP 0.011 TYP			0.320 TYP			0.013 TYP						
K2	0.200 TYP				0.008 TYP		0.200 BSC			0.008 TYP			
К3	0.255 TYP 0.010 TYP)										
K4	0.300 TYP			0.012 TYP									
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014	
Т							0.03	0.08	0.13	0.001	0.003	0.005	
ECN: C-(17/31 Be	v C 06-Au	a-07		ı	ı	ı	1		ı	1		

ECN: C-07431 - Rev. C, 06-Aug-07

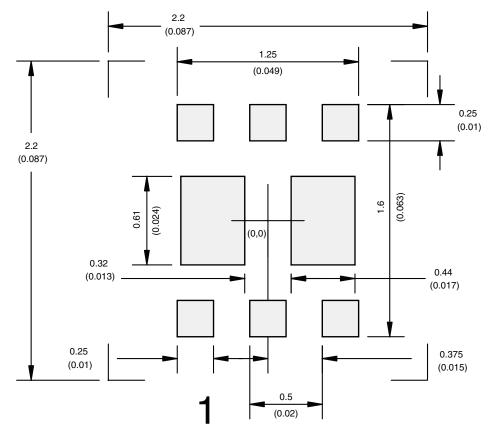
DWG: 5935

Document Number: 73000 06-Aug-07

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RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Dual



Dimensions in mm/(Inches)

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APPLICATION NOTE



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